

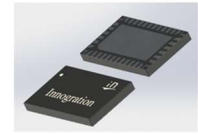


GaN HEMT 28V, 2450MHz 30W, RF Power Transistor

GTAH25030C6

Description

The GTAH25030C6 is a 30W GaN HEMT, designed for ISM/RF Energy application at 2.45GHz. The transistor is available in a highly cost effective 10*6mm, surface mount, QFN package with 100% production test to ensure the quality and consistency.



It can be used in CW, Pulse and any other modulation modes.

There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

- Typical Class AB RF Performance with device soldered through high density and plated grounding vias

V_{ds} = 28V, I_{dq} = 10mA, V_{gs} = -2.5V, CW

Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff (%)	P1dB Gain (dB)	P3dB (dBm)	P3dB (W)	P3dB Eff (%)
2400	44.65	29.2	73.0	20.1	45.35	34.2	78
2450	43.84	24.2	71.2	19.4	44.82	30.3	79
2500	43.32	21.5	70.4	17.7	44.5	28.2	78

V_{ds} = 32V, I_{dq} = 10mA, V_{gs} = -2.5V, CW

Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff (%)	P1dB Gain (dB)	P3dB (dBm)	P3dB (W)	P3dB Eff (%)
2400	45.73	37.4	71.7	20.3	46.35	43.1	76
2450	45.03	31.8	70.6	19.8	45.88	38.8	77
2500	44.63	29.1	71.5	18.2	45.59	36.3	78

Applications

- S band power amplifier
- ISM/RF Energy power amplifier

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

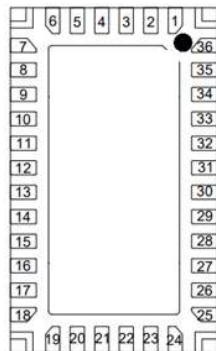
1. Set V_{GS} to the pinch-off (V_P) voltage, typically -5 V
2. Turn on V_{DS} to nominal supply voltage
3. Increase V_{GS} until I_{DS} current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce V_{GS} down to V_P, typically -5 V
3. Reduce V_{DS} down to 0 V
4. Turn off V_{GS}

Figure 1: Pin Connection definition

Transparent top view (Backside grounding for source)



Pin No.	Symbol	Description
8,9,10,11,14,15,16,17	RF IN/Vgs	RF Input, Vgs bias



26,27,28,29,32,33,34,35	RF OUT/VDD	RFOutput, Drain bias
Rest Pins and Package Base	GND	DC/RF Ground. Must be soldered directly to heatsink or copper coin for CW application.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	+150	Vdc
Gate--Source Voltage	V_{GS}	-8 to +0.5	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum gate current	I_{gs}	12	mA
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case by FEA $T_C = 85^\circ\text{C}$, at $P_{diss} = 8\text{W}$	$R_{\theta JC}$	3.8	°C /W

Table 3. Electrical Characteristics (TA = 25°C unless otherwise noted)

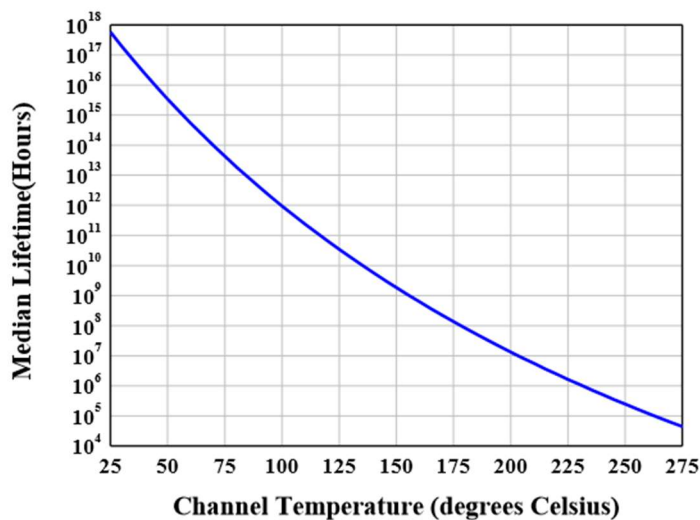
DC Characteristics (main path, measured on wafer prior to packaging)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = -8\text{V}$; $I_{DS} = 8\text{mA}$	V_{DSS}		200		V
Gate Threshold Voltage	$V_{DS} = 10\text{V}$, $I_D = 8\text{mA}$	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	$V_{DS} = 28\text{V}$, $I_{DS} = 30\text{mA}$, Measured in Functional Test	$V_{GS(Q)}$		-2.5		V

Ruggedness Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Load mismatch capability	2.5GHz, $P_{out} = 30\text{W}$ Pulsed CW All phase, No device damages	VSWR		10:1		

Figure 2: Median Lifetime vs. Channel Temperature

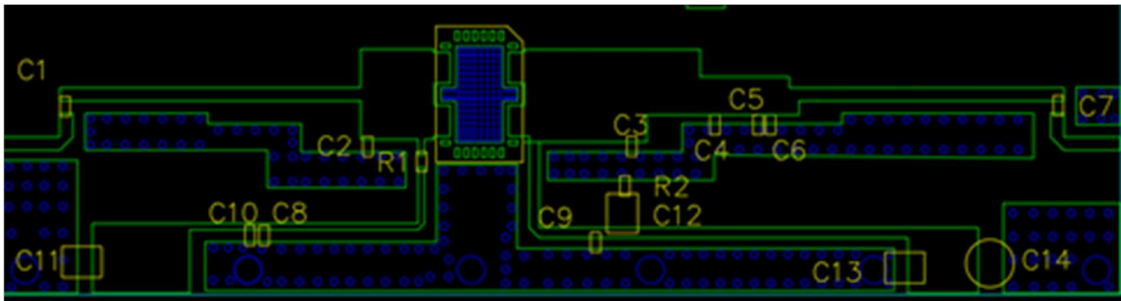


Typical performance

Figure 3: Network analyzer output S11/S21



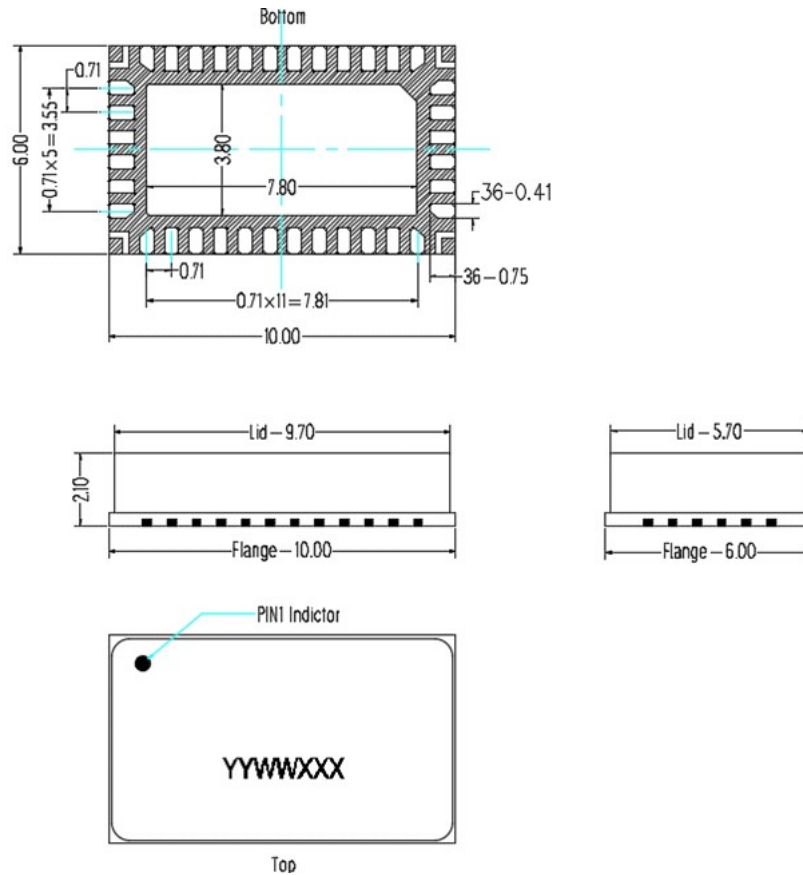
Table 4. Bill of materials of application board (PCB layout upon request, RO4350B 20mils)



Component	Value	Quantity
U1	GTAH25030C6	1
C1	5.1pF	1
C7、C8、C9	12pF	3
C10	10uF/16V	1
C11、C12、C13	10uF/63V	3
R1、R2	10 Ω	2
C14	470uF/63V	1
C2	1pF	1
C3	1.2pF	1
C4、C5、C6	0.5pF	3



10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are ± 0.2 mm.

Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2023/12/29	V1.0	Preliminary Datasheet Creation

Application data based on: ZYX-23-13

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